

# InP Non dope 4" wafer



Parameter	Customer's Requirements	UOM
Material	InP	
Growth Method	VGF	
Conduct Type	SI	
Dopant	N/A	
Diameter	100±0.5	mm
Orientation	(100)	
Orientation Angle	N/A	
OF Location/Length	(0-1-1)±0.5° / N/A	
IF Location/Length	(0-11) / N/A	
Ingot CC	Min: N/A      Max: N/A	/cm <sup>3</sup>
Resistivity	Min: N/A      Max: N/A	Ω.cm
Mobility	Min: N/A      Max: N/A	/cm <sup>2</sup> /v.s
EPD	Max: N/A	/cm <sup>2</sup>
Thickness	Min: 700      Max: 750	μm
Edge Rounding	N/A	mmR
Laser Marking	N/A	
TTV/TIR	Max: N/A	μm
BOW	Max: N/A	μm
Warp	Max: N/A	μm
Surface Finish-front	Polished	
Surface Finish-Back	Etched	
Particle Count	N/A	
Epi-Ready	N/A	